wherein (σ_i) is stress in said i-th insulating film and is positive when tensile stress and negative when compressive stress.
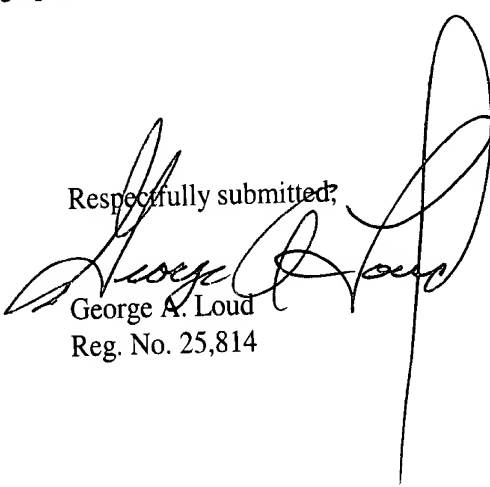
REMARKS

The present amendment to claim 43 serves to correct an obvious typographical error. The corrected language is the same as that of applicants' original disclosure. See, for example, page 17, lines 32-37 and claim 2 of applicants' original specification.

It is believed that correction of the typographical error obviates all of the rejections under 35 USC 112.

Respectfully submitted,

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43. (Amended Three Times) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising:

(a) forming a first insulating layer with compressive stress;

(b) forming an aluminum interconnection layer on and in contact with said first insulating layer;

(c) forming a second insulating layer with compressive stress on and in contact with said interconnection layer;

wherein said interconnection layer is sandwiched between and in contact with said first insulating layer and said second insulating layer and wherein the total stress in said insulating layers is limited to less than 2×10^5 dyne/cm so as to suppress bending of said interconnection layer; and

(d) before forming said first insulating layer or after forming said second insulating layer, forming a third insulating layer with tensile stress, so as to adjust overall stress of said stress-adjusted insulating film;

wherein the stress-adjusted insulating film has first through i-th insulating layers having the thickness t_1 through t_i, respectively, and wherein the thickness (t_i) of i-th insulating layer of said stress-adjusted film is determined so as not to exceed stress (σ_T) of said overall stress-adjusted insulating film where said stress (σ_T) is calculated as:

$$\sigma_T = \sum_{i=1}^{n} (t_i \times \sigma_i)$$

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wherein $(\underline{\sigma_i})$ $[(\sigma_T)]$ is stress in said i-th insulating film and is positive when tensile stress and

negative when compressive stress.